

Features:

- New SOI CMOS Technology
- No DC Blocking Capacitors Required
- 2-Bit Control, Low Control Voltage
- High ESD Rating of 1.2KV (HBM)

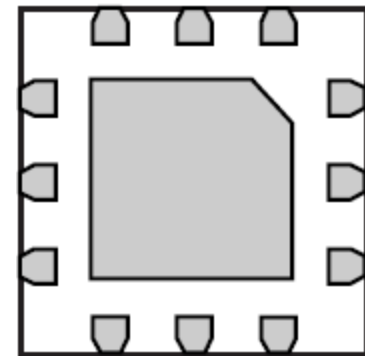
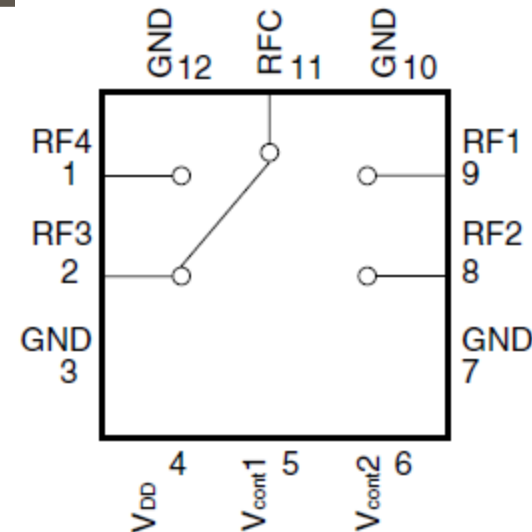
Applications:

- GSM / UMTS / 3G/4G/LTE Antenna Switching
- Band Switching / Antenna Tuning
- Femto Cells / Small Cells
- General High Power RF Applications up to +35dBm and 6GHz

RF Performance (Typical):

- Operating Frequency: 0.05 to **6.0**GHz
- Low Control voltage: **1.3V**, Vdd=2.3V min.
- Insertion Loss: 0.40dB at 1GHz, 0.5dB at 2GHz
- Isolation: 35 at 1GHz, 30dB 2GHz
- P(0.1dB) **+38**dBm
- 2fo/3fo: -80/-75dBc @+35dBm, 0.9GHz
- 2fo/3fo: -85/-80dBc @+33dBm, 1.8GHz

(Top View)



12pin Plastic QFN Package
2.0 x 2.0 x 0.6 mm
Lead Pitch 0.5 mm